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(54) **Semiconductor laser device having InGaAs compressive-strain active layer, GaAsP tensile-strain barrier layers and InGaP optical waveguide layers**

Halbleiterlaservorrichtung mit einer aktiven Schicht aus InGaAs unter Kompressionsdruck, einer Sperrschicht aus GaAsP unter Dehnungsdruck, und einem Lichtwellenleiter aus InGaP

Laser semiconducteur doté d'une couche active d'InGaAs en compression, d'une barrière en GaAsP sous tension et d'un guide d'onde en InGaP

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Note: Within nine months from the publication of the mention of the grant of the European patent, any person may give notice to the European Patent Office of opposition to the European patent granted. Notice of opposition shall be filed in a written reasoned statement. It shall not be deemed to have been filed until the opposition fee has been paid. (Art. 99(1) European Patent Convention).

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